

GaAlAs T-1 3/4 PACKAGE

INFRARED EMITTING DIODE

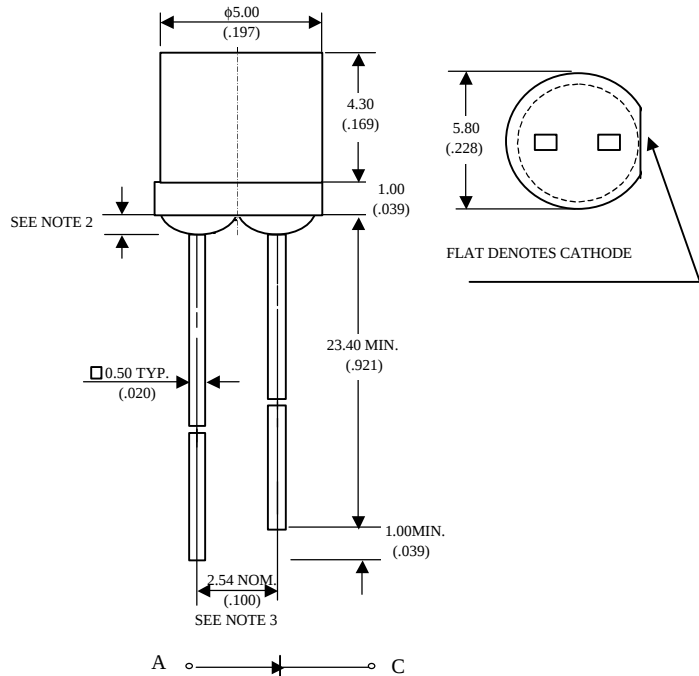
MIE-824H2

Description

The MIE-824H2 is a GaAlAs infrared LED having a peak wavelength at 850nm. It features ultra-high power, high response speed and molded package with higher radiant intensity. In addition to improving the S/N ratio in applied optical systems, the MIE-824H2 has greatly improved long-distance characteristics as well as significantly increased its range of applicability .

Package Dimensions

Unit: inches



Features

- Ultra-High radiant intensity
- High response speed
- Standard T-1 3/4 (f 5mm) package, radiant angle : 80°
- Peak wavelength $\lambda_p = 850$ nm

Notes :

1. Tolerance is ± 0.25 mm (.010") unless otherwise noted.
2. Protruded resin under flange is 1.5 mm (.059") max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ $T_A = 25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	150	mW
Peak Forward Current	1	A
Continuous Forward Current	100	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to $+100^\circ\text{C}$	
Storage Temperature Range	-55°C to $+100^\circ\text{C}$	
Lead Soldering Temperature	260°C for 5 seconds	

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Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ .	Max.	Unit
Radiant Intensity	I _F =20mA	I _e		0.5		mW/sr
Forward Voltage	I _F =50mA	V _F		1.5	1.8	V
Reverse Current	V _R =5V	I _R			10	μA
Peak Wavelength	I _F =20mA	λ		850		nm
Spectral Bandwidth	I _F =20mA	Δλ		30		nm
View Angle	I _F =20mA	2 θ _{1/2}		120		deg .
Rise Time	I _F =50mA	Tr		20		nsec
Fall Time	I _F =50mA	Tf		30		nsec

Typical Optical-Electrical Characteristic Curves

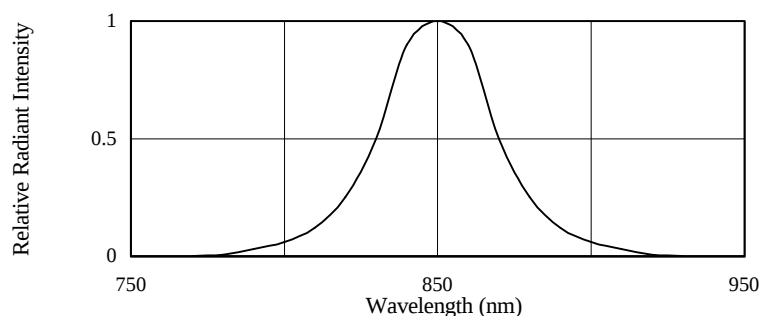


FIG.1 SPECTRAL DISTRIBUTION

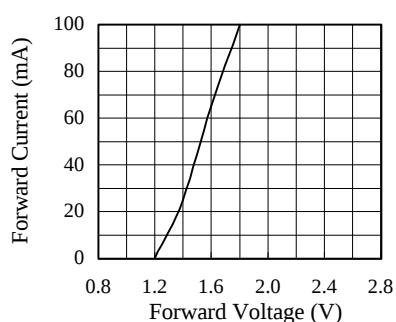


FIG.2 FORWARD CURRENT VS. FORWARD VOLTAGE

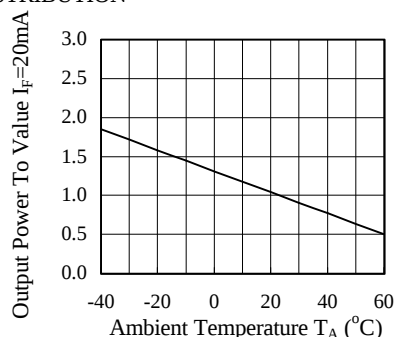


FIG.3 RELATIVE RADIANT INTENSITY VS. AMBIENT TEMPERATURE

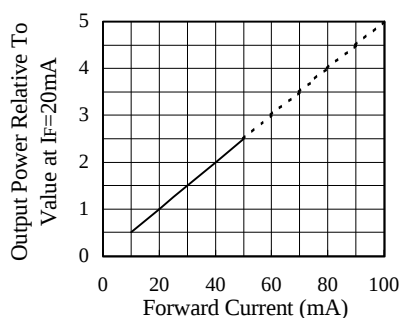


FIG.4 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

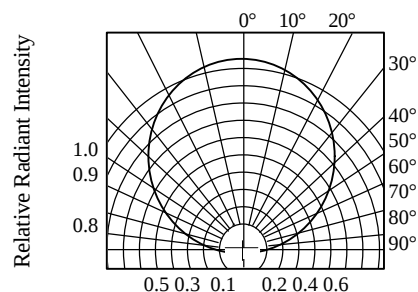


FIG.5 RADIATION DIAGRAM